

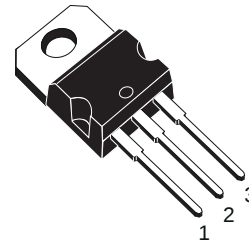
COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES

DESCRIPTION

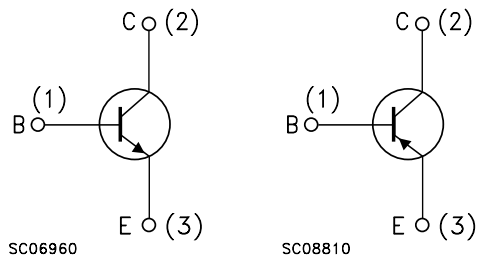
The BD909 and BD911 are silicon Epitaxial-Base NPN power transistors mounted in Jedec TO-220 plastic package. They are intended for use in power linear and switching applications.

The complementary PNP types are BD910 and BD912 respectively.



TO-220

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	PNP	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	80	100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	80	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I_E, I_C	Collector Current	15		A
I_B	Base Current	5		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	90		W
T_{stg}	Storage Temperature	-65 to 150		$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150		$^\circ\text{C}$

For PNP types voltage and current values are negative.

BD909 / BD910 / BD911 / BD912

THERMAL DATA

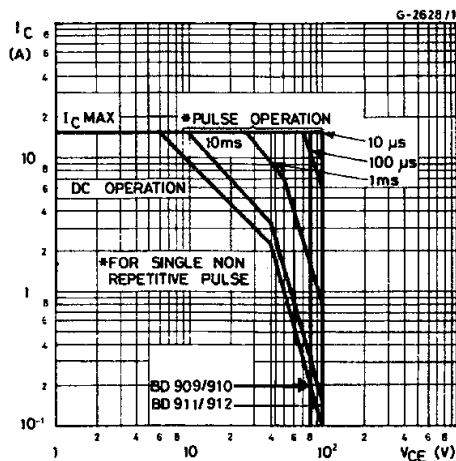
R _{thj-case}	Thermal Resistance Junction-case	Max	1.4	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

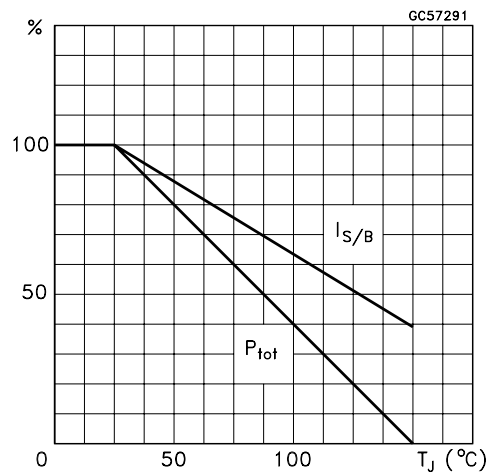
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	for BD909/910 V _{CB} = 80 V for BD911/912 V _{CB} = 100 V T _{case} = 150 °C for BD909/910 V _{CB} = 80 V for BD911/912 V _{CB} = 100 V			500 500 5 5	μA μA mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for BD909/910 V _{CE} = 40 V for BD911/912 V _{CE} = 50 V			1 1	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA for BD909/910 for BD911/912	80 100			V V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 5 A I _B = 0.5 A I _C = 10 A I _B = 2.5 A			1 3	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 10 A I _B = 2.5 A			2.5	V
V _{BE*}	Base-Emitter Voltage	I _C = 5 A V _{CE} = 4 V			1.5	V
h _{FE*}	DC Current Gain	I _C = 0.5 A V _{CE} = 4 V I _C = 5 A V _{CE} = 4 V I _C = 10 A V _{CE} = 4 V	40 15 5		250 150	
f _T	Transition frequency	I _C = 0.5 A V _{CE} = 4 V	3			MHz

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

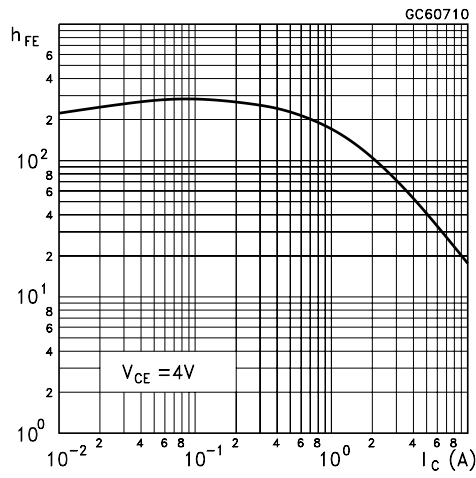
Safe Operating Area



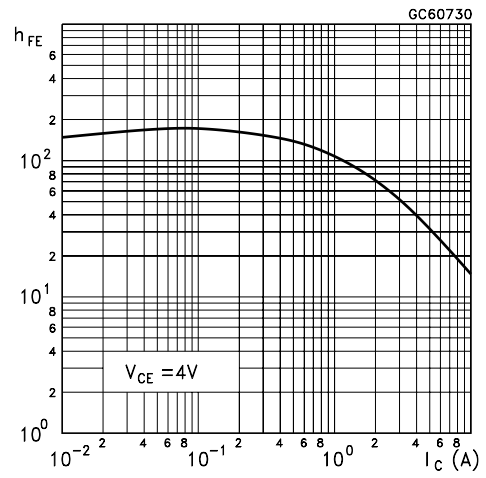
Derating Curves



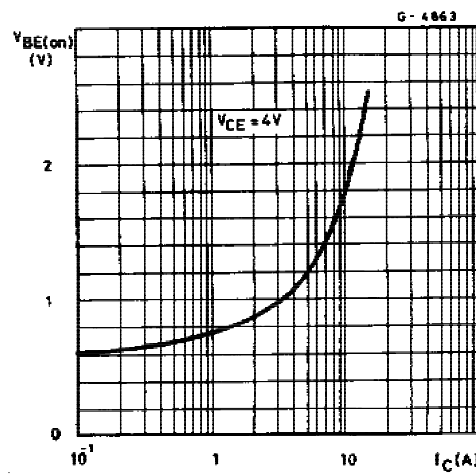
DC Current Gain (NPN type)



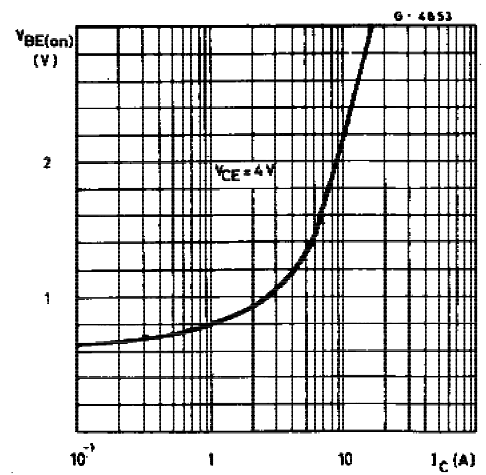
DC Current Gain (PNP type)



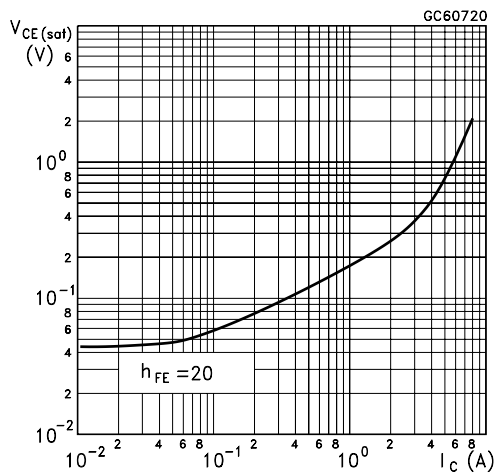
DC Transconductance (NPN type)



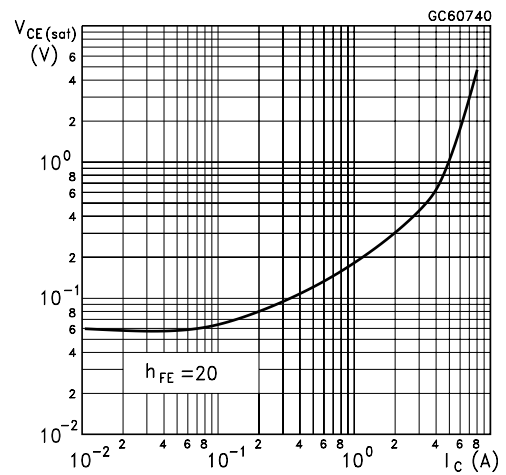
DC Transconductance (PNP type)



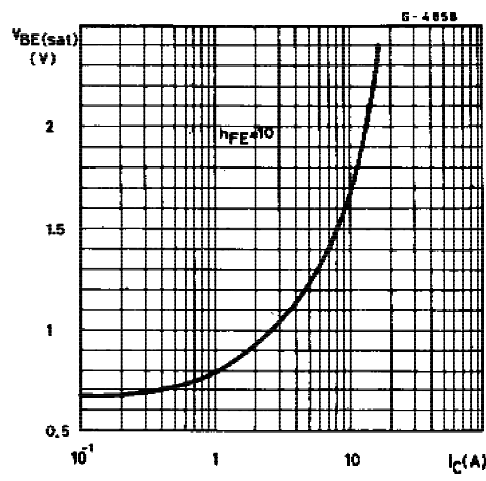
Collector-Emitter Saturation Voltage (NPN type)



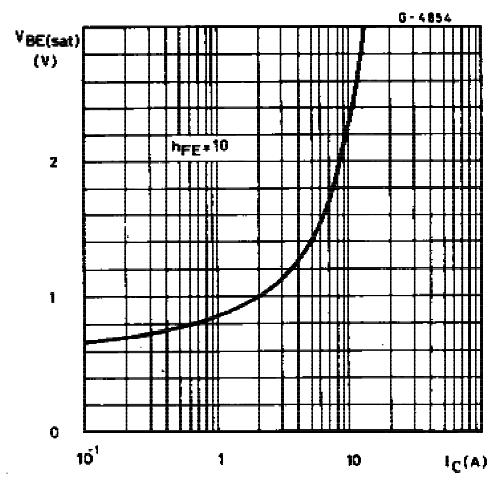
Collector-Emitter Saturation Voltage (PNP type)



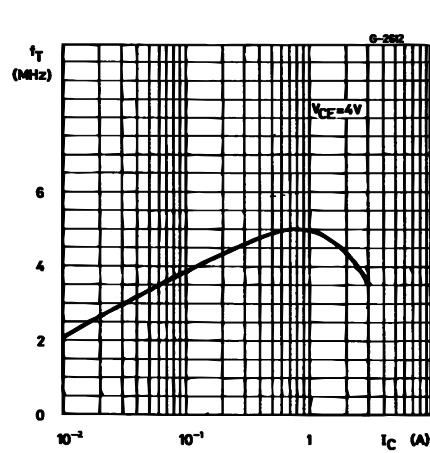
Base-Emitter Saturation Voltage (NPN type)



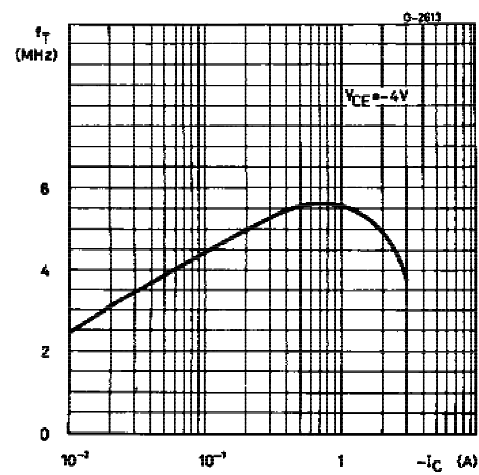
Base-Emitter Saturation Voltage (PNP type)



Transition Frequency (NPN type)

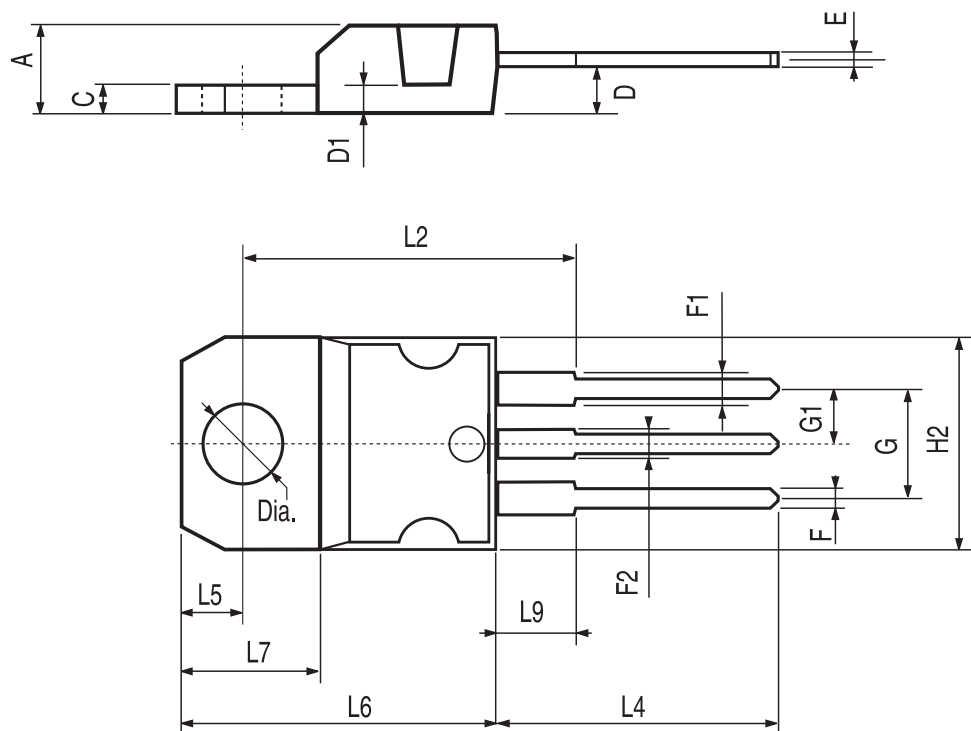


Transition Frequency (PNP type)



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

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